

Schottky Barrier Rectifier

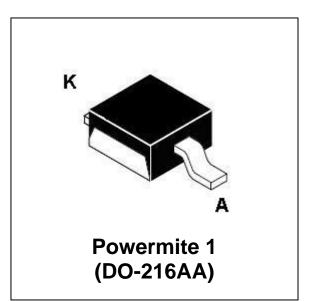
Main product characteristics

Ι _ο	1A		
V _{RRM}	20V		
T _{j(MAX)}	150°C		
V _{F(MAX)}	0.45V		

Features and benefits

- Low forward voltage drop
- Low profile package height
- Efficient heat path with integral locking bottom metal tab
- Low thermal resistance DO-216AA package

Description and applications



Single schottky rectifier assembled in Powermite 1[®] package which features a full metallic bottom that eliminates possibility of solder flux entrapment during assembly. The package also incorporates a unique locking tab which acts as an efficient heat path from die to mounting plane for external heat sinking with very low thermal resistance junction to case (bottom).

This product is suitable for use in switching and regulating power supplies and also charge pump circuits.

Absolute maximum ratings⁽¹⁾

Symbol	Parameter	Value	Unit		
V _{RRM} V _{RWM} V _R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vorking Peak Reverse Voltage 20			
V _{R(RMS)}	RMS Reverse Voltage				
I ₀	Average rectified forward output current (T _c = 135°C)	1.0	A		
I _{FRM}	Peak repetitive forward current (100kHz square wave, T _c = 135°C)	2.0	A		
I _{FSM}	Non repetitive peak forward surge current (8.3ms single half sine wave)	50	А		
dV/dt	Voltage rate of change (at max V_R)	10000	V/µs		
T _{STG}	Storage temperature	-55 to +150	°C		
TJ	Junction temperature	-55 to +150	°C		

⁽¹⁾ All ratings at 25°C unless specified otherwise



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Characteristics

Static Electrical Characteristics

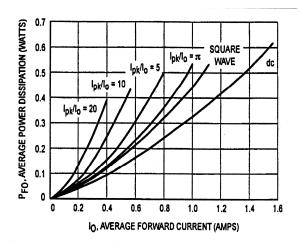
Symbol	Parameter	Test Conditions		Тур	max	Units
$V_{F}^{(2)}$	Maximum forward voltage	T _J = 25°C	I _F = 1.0 A		0.45	V
I _R ⁽²⁾	Maximum instantaneous reverse current	T _J = 25°C	V _R = 20V		1.0	mA
Ст	Junction capacitance	V _R = 5V, f = 1MHz		105		pF

⁽²⁾ Measured with a test pulse of 380µs to minimize self-heating effect

Thermal Characteristics

Symbol	Parameter	Value	Unit	
R _{ØJC}	Junction to case (bottom)	15	°C/W	
R _{OJA}	Junction to ambient ⁽³⁾	240	°C/W	

⁽³⁾ Mounted on FR-4 PC board using 1oz copper with recommended minimum foot print



Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation:

 $T_J = T_{J max} = r(t)(Pf+Pr)$ where

r(t) = thermal impedance under given conditions.

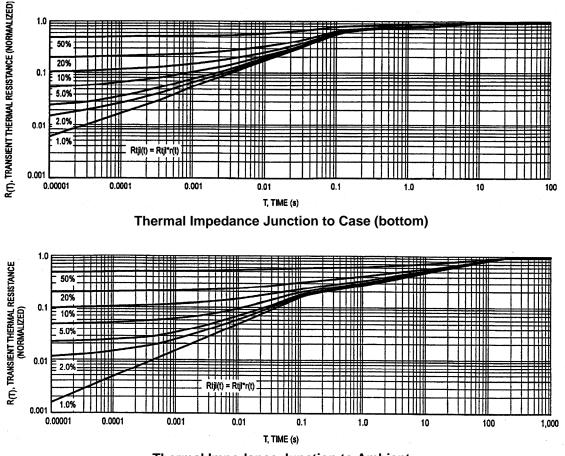
Pf = forward power dissipation, and

Pr = reverse power dissipation

This graph displays the de-rated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{J \text{ max}}-r(t) Pr$, Where r(t)=Rthja. For other power applications further calculations must be performed.



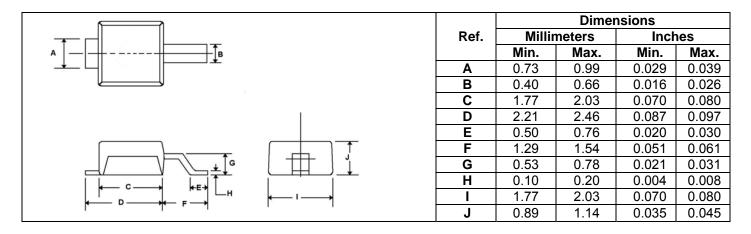
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Thermal Impedance Junction to Ambient

Mechanical Characteristics

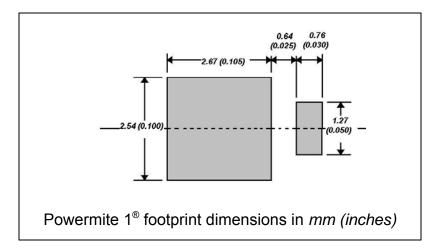
Physical dimensions





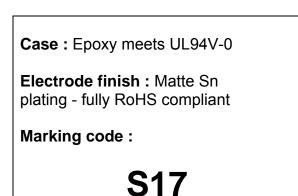
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Footprint dimensions



Ordering information

Package materials & information



Product order code	Marking	Package	Weight	Base qty	Delivery mode
UPS5817e3 / TR7	S17	Powermite 1 (DO-216AA)	0.016 g	3000	Tape and reel (7 inch)
UPS5817e3 / TR13	S17	Powermite 1 (DO-216AA)	0.016 g	12000	Tape and reel (13 inch)

Commercial Business Unit Microsemi Corporation

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Please refer to www.microsemi.com for the terms and conditions of purchase